

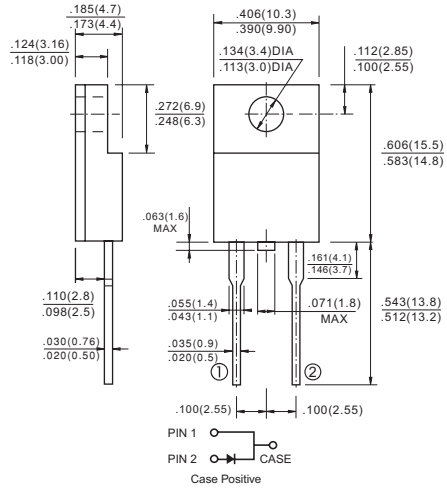


Features

- ✧ Glass passivated chip junction.
- ✧ High efficiency, Low VF
- ✧ High current capability
- ✧ High reliability
- ✧ High surge current capability
- ✧ For use in low voltage, high frequency inverter, free wheeling, and polarity protection application.

Mechanical Data

- ✧ Cases: ITO-220AC molded plastic
- ✧ Epoxy: UL 94V0 rate flame retardant
- ✧ Terminals: Pure tin plated, lead free solderable per MIL-STD-202, Method 208 guaranteed
- ✧ Polarity: As marked
- ✧ High temperature soldering guaranteed: 260°C/ 0.25" (6.35mm) from case for 10 seconds
- ✧ Mounting torque: 5 in – 1bs. Max.
- ✧ Weight: 2.24 grams



Dimensions in inches and (millimeters)

Maximum Rating and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%

Type Number	Symbol	HERAF 801G	HERAF 802G	HERAF 803G	HERAF 804G	HERAF 805G	HERAF 806G	HERAF 807G	HERAF 808G	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current .375"(9.5mm) Lead Length @ $T_C = 100^\circ C$	$I_{(AV)}$	8.0								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	150								A
Maximum Instantaneous Forward Voltage @8.0A	V_F	1.0		1.3		1.7			V	
Maximum DC Reverse Current @ $T_A = 25^\circ C$ at Rated DC Blocking Voltage @ $T_A = 125^\circ C$	I_R	10 400								μA μA
Maximum Reverse Recovery Time (Note 1)	T_{rr}	50			80			nS		
Typical Junction Capacitance (Note 2)	C_j	80			60			pF		
Typical Thermal resistance (Note 3)	$R_{\theta JC}$	2.0								$^\circ C/W$
Operating Temperature Range	T_J	-65 to +150								$^\circ C$
Storage Temperature Range	T_{STG}	-65 to +150								$^\circ C$

- Notes: 1. Reverse Recovery Test Conditions: $I_F = 0.5A$, $I_R = 1.0A$, $I_{RR} = 0.25A$
2. Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.
3. Mounted on Heatsink Size of 2 in x 3 in x 0.25 in Al-Plate.

RATINGS AND CHARACTERISTIC CURVES (HERAF801G THRU HERAF808G)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

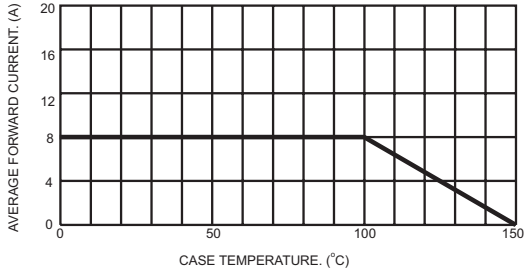


FIG.2- TYPICAL REVERSE CHARACTERISTICS

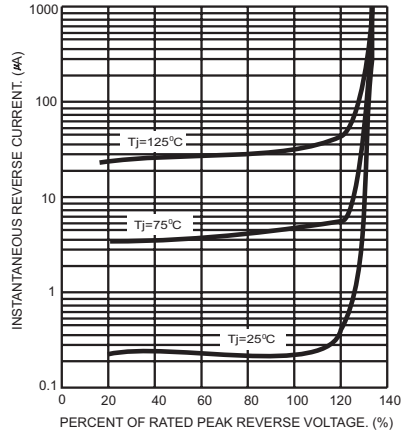


FIG.3- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

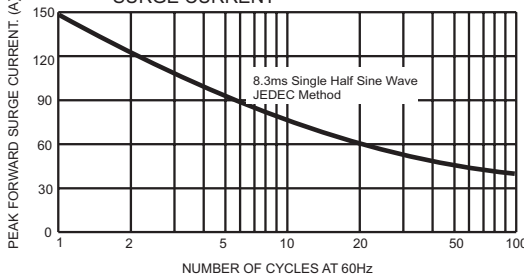


FIG.5- TYPICAL FORWARD CHARACTERISTICS

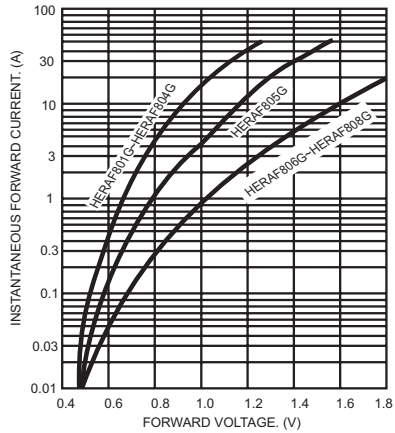


FIG.4- TYPICAL JUNCTION CAPACITANCE

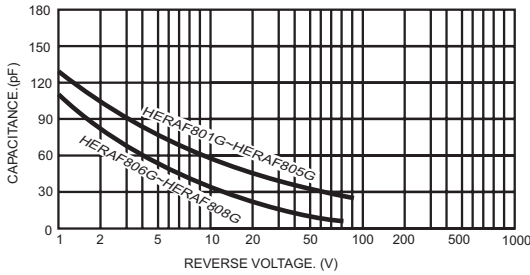
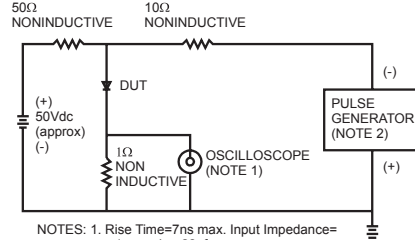


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



NOTES: 1. Rise Time=7ns max. Input Impedance= 1 megohm 22pf
2. Rise Time=10ns max. Source Impedance= 50 ohms

